N-Channel 80-V (D-S) MOSFET

Key Features:

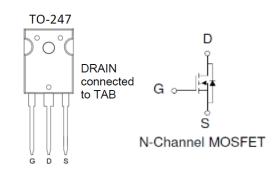
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- · LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	In (A)		
80	1.8 @ V _{GS} = 10V	200 ^a		
60	$2.3 @ V_{GS} = 4.5V$	200		





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		V_{DS}	80	V		
Gate-Source Voltage		V_{GS}	±20	V		
Continuous Drain Current a	T _C =25°C	I _D	200	Α		
Pulsed Drain Current ^b		I _{DM}	800	A		
Continuous Source Current (Diode Conduction) a	T _C =25°C	I _S	200	Α		
Power Dissipation ^a	T _C =25°C	P_D	500	W		
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Maximum	Units	
Maximum Junction-to-Ambient °	$R_{\theta JA}$	40	°C/W	
Maximum Junction-to-Case	$R_{\theta JC}$	0.29	C/VV	

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Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

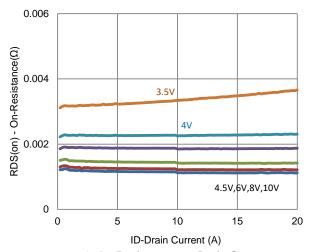
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	l	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10 u		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α	
Dunin Course On Booistones 8	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			1.8	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$			2.3		
Forward Transconductance a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		71		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 20 A, V _{GS} = 0 V		0.82		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 40 \text{ V}, V_{GS} = 4.5 \text{ V},$		77		nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 20 \text{ A}$		25			
Gate-Drain Charge	Q_gd	1 _D = 23 / X		33		1	
Turn-On Delay Time	t _{d(on)}	V 40 V B = 2.0		34			
Rise Time	t _r	$V_{DS} = 40 \text{ V}, R_{L} = 2 \Omega,$ $I_{D} = 20 \text{ A},$		36		200	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		216		ns	
Fall Time	t _f	V GEN = 10 V, NGEN = 0 12		153			
Input Capacitance	C _{iss}			5976			
Output Capacitance	C_{oss}	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		1279		рF	
Reverse Transfer Capacitance	C_{rss}			879			

Notes

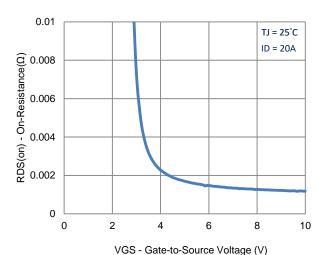
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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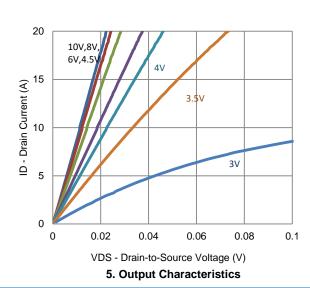
Typical Electrical Characteristics

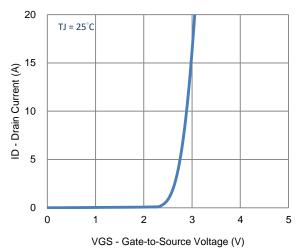


1. On-Resistance vs. Drain Current

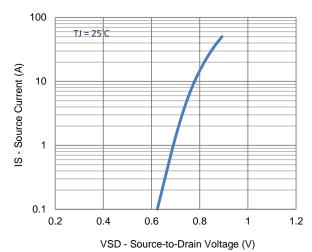


3. On-Resistance vs. Gate-to-Source Voltage

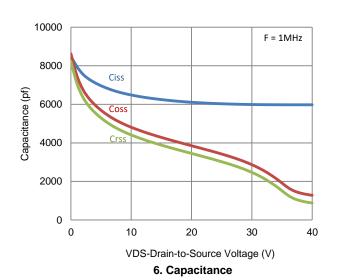




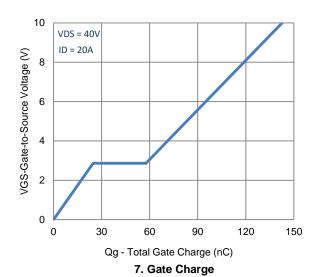
2. Transfer Characteristics

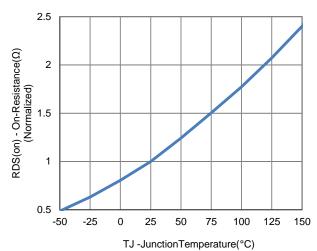


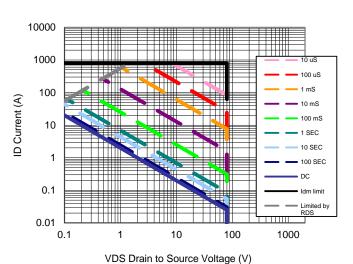
4. Drain-to-Source Forward Voltage



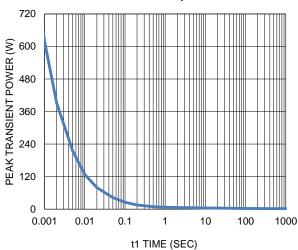
Typical Electrical Characteristics





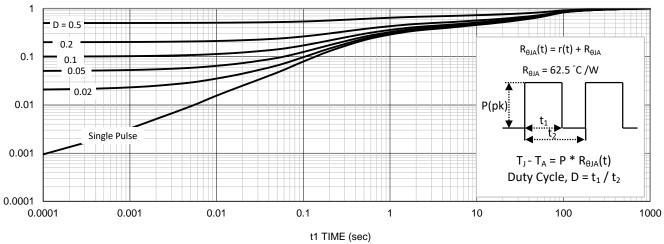


8. Normalized On-Resistance Vs Junction Temperature



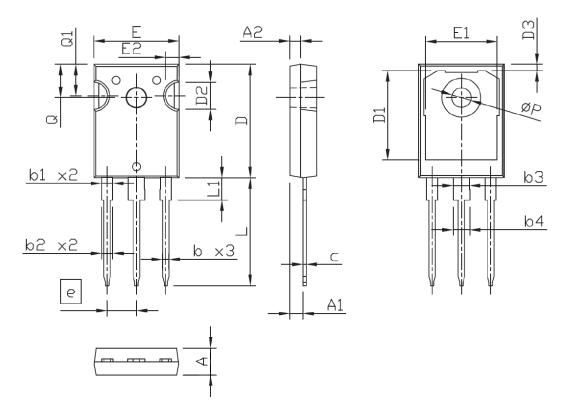
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS				
SIMBULS	MIN	NDM	MAX		
Α	4,90	5,00	5,10		
A1	2.32	2.42	2.52		
A2	1,90	2,00	2,10		
b	1.17	1.22	1.27		
b1	1.97	2,02	2.07		
b2	2.00	2.10	2.20		
b3	2.97	3.02	3.07		
b4	3.00	3.10	3.20		
C	0.59	0.62	0.66		
D	20,90	21.00	21,10		
D1	16.25	16.55	16.85		
D5		5,00 TYP)		
D3	1.05	1.20	1.35		
е		5,44 BS0			
E	15.70	15.80	15.90		
E1	13.06	13.26	13.46		
E2	2,50 TYP				
L	19.72	19.92	20.12		
L1			4,30		
Q	6.15 BSC				
Q1	5.60	5,80	6.00		
ØΡ	3.55	3.60	3.65		